

4-Mbit (512K x 8) Static RAM

Features

- **Temperature Ranges**
 - Commercial: 0°C to 70°C
 - Industrial: -40°C to 85°C
 - Automotive: -40°C to 125°C
- **High speed**
 - $t_{AA} = 10$ ns
- **Low active power**
 - 324 mW (max.)
- **2.0V data retention**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with CE and OE features**

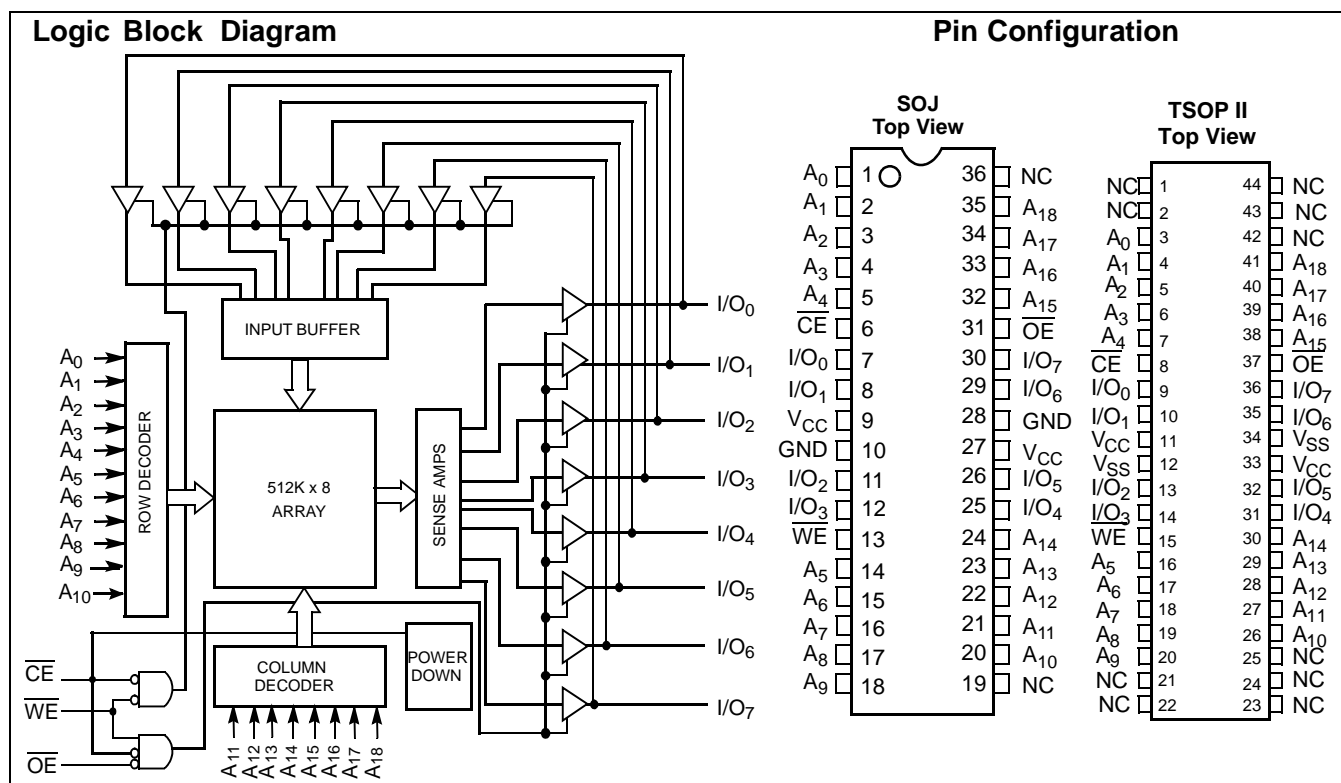
Functional Description^[1]

The CY7C1049CV33 is a high-performance CMOS Static RAM organized as 524,288 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable (\overline{CE}), an active LOW Output Enable (\overline{OE}), and three-state drivers. Writing to the device is accomplished by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{18}).

Reading from the device is accomplished by taking Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing Write Enable (\overline{WE}) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (\overline{CE} HIGH), the outputs are disabled (\overline{OE} HIGH), or during a Write operation (\overline{CE} LOW, and \overline{WE} LOW).

The CY7C1049CV33 is available in standard 400-mil-wide 36-pin SOJ package and 44-pin TSOP II package with center power and ground (revolutionary) pinout.



Notes:

1. For guidelines on SRAM system design, please refer to the 'System Design Guidelines' Cypress application note, available on the internet at www.cypress.com.

Selection Guide

		-8 ¹	-10	-12	-15	Unit
Maximum Access Time		8	10	12	15	ns
Maximum Operating Current	Commercial	100	90	85	80	mA
	Industrial	110	100	95	90	mA
	Automotive	-	-	-	95	mA
Maximum CMOS Standby Current	Commercial / Industrial	10	10	10	10	mA
	Automotive	-	-	-	15	mA

Shaded areas contain advance information.

Pin Definitions

Pin Name	36-SOJ Pin Number	44 TSOP-II Pin Number	I/O Type	Description
A ₀ -A ₁₈	1-5,14-18, 20-24,32-35	3-7,16-20, 26-30,38-41	Input	Address Inputs used to select one of the address locations.
I/O ₀ - I/O ₇	7,8,11,12,25, 26,29,30	9,10,13,14, 31,32,35,36	Input/Output	Bidirectional Data I/O lines. Used as input or output lines depending on operation
NC ^[2]	19,36	1,2,21,22,23, 24,25,42,43, 44	No Connect	No Connects. This pin is not connected to the die
WE	13	15	Input/Control	Write Enable Input, active LOW. When selected LOW, a WRITE is conducted. When selected HIGH, a READ is conducted.
CE	6	8	Input/Control	Chip Enable Input, active LOW. When LOW, selects the chip. When HIGH, deselects the chip.
OE	31	37	Input/Control	Output Enable, active LOW. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are three-stated, and act as input data pins.
V _{SS} , GND	10,28	12,34	Ground	Ground for the device. Should be connected to ground of the system.
V _{CC}	9,27	11,33	Power Supply	Power Supply inputs to the device.

Notes:

2. NC pins are not connected on the die.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied -55°C to +125°C

Supply Voltage on V_{CC} to Relative GND^[3] -0.5V to +4.6V

DC Voltage Applied to Outputs

in High-Z State^[3] -0.5V to $V_{CC} + 0.5V$

DC Input Voltage^[3] -0.5V to $V_{CC} + 0.5V$

Current into Outputs (LOW) 20 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	3.3V ± 0.3V
Industrial	-40°C to +85°C	
Automotive	-40°C to +125°C	

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		-8 ¹		-10		-12		-15		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	V _{CC} = Min.; I _{OH} = −4.0 mA		2.4		2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min.; I _{OL} = 8.0 mA			0.4		0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	V
V _{IL}	Input LOW Voltage ^[3]			−0.3	0.8	−0.3	0.8	−0.3	0.8	−0.3	0.8	V
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	Com'I / Ind'I	−1	+1	−1	+1	−1	+1	−1	+1	μA
			Automotive	-	-	-	-	-	-	−20	+20	μA
I _{OZ}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{CC} , Output Disabled	Com'I / Ind'I	−1	+1	−1	+1	−1	+1	−1	+1	μA
			Automotive	-	-	-	-	-	-	−20	+20	μA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., f = f _{MAX} = 1/t _{RC}	Com'I		100		90		85		80	mA
			Ind'I		110		100		95		90	mA
			Automotive		-		-		-		95	mA
I _{SB1}	Automatic CE Power-down Current —TTL Inputs	Max. V _{CC} , CE ≥ V _{IH} ; V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}	Com'I / Ind'I		40		40		40		40	mA
			Automotive		-		-		-		45	mA
I _{SB2}	Automatic CE Power-down Current —CMOS Inputs	Max. V _{CC} , CE ≥ V _{CC} − 0.3V, V _{IN} ≥ V _{CC} − 0.3V, or V _{IN} ≤ 0.3V, f = 0	Com'I/Ind'I		10		10		10		10	mA
			Automotive		-		-		-		15	mA

Capacitance^[4]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{CC} = 3.3V$	8	pF
C_{OUT}	I/O Capacitance		8	pF

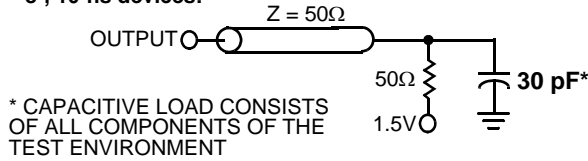
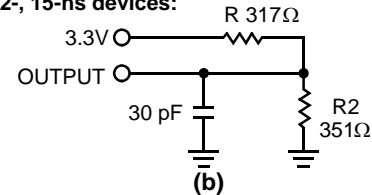
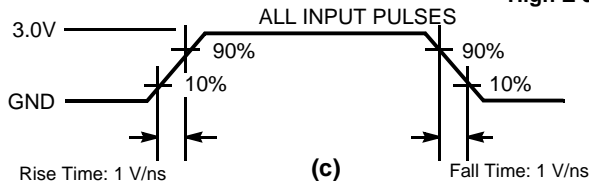
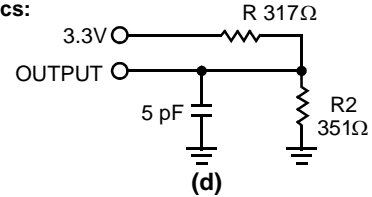
Thermal Resistance^[4]

Parameter	Description	Test Conditions	36-pin SOJ (Non Pb-Free)	36-pin SOJ (Pb-Free)	44-TSOP-II (Non Pb-Free)	44-TSOP-II (Pb-Free)	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51.	46.51	46.51	41.66	41.66	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		18.8	18.8	10.56	10.56	°C/W

Notes:

3. $V_{IL}(\text{min.}) = -2.0V$ and $V_{IH}(\text{max.}) = V_{CC} + 0.5V$ for pulse durations of less than 20 ns.

4. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms^[5]
8-, 10-ns devices:

(a)
12-, 15-ns devices:

(b)
High-Z characteristics:

(c)

(d)
AC Switching Characteristics^[6] Over the Operating Range

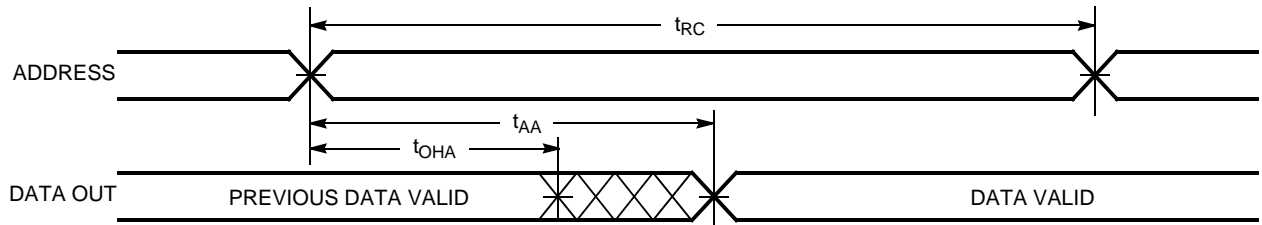
Parameter	Description	-8 ^[1]		-10		-12		-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t _{power} ^[7]	V _{CC} (typical) to the first access	1		1		1		1		μs
t _{RC}	Read Cycle Time	8		10		12		15		ns
t _{AA}	Address to Data Valid		8		10		12		15	ns
t _{OHA}	Data Hold from Address Change	3		3		3			3	ns
t _{ACE}	CE LOW to Data Valid		8		10		12		15	ns
t _{DOE}	OE LOW to Data Valid		4		5		6		7	ns
t _{LZOE}	OE LOW to Low-Z	0		0		0		0		ns
t _{HZOE}	OE HIGH to High-Z ^[8, 9]		4		5		6		7	ns
t _{LZCE}	CE LOW to Low-Z ^[9]	3		3		3		3		ns
t _{HZCE}	CE HIGH to High-Z ^[8, 9]		4		5		6		7	ns
t _{PU}	CE LOW to Power-up	0		0		0		0		ns
t _{PD}	CE HIGH to Power-down		8		10		12		15	ns
Write Cycle ^[10, 11]										
t _{WC}	Write Cycle Time	8		10		12		15		ns
t _{SCE}	CE LOW to Write End	6		7		8		10		ns
t _{AW}	Address Set-up to Write End	6		7		8		10		ns
t _{HA}	Address Hold from Write End	0		0		0		0		ns
t _{SA}	Address Set-up to Write Start	0		0		0		0		ns
t _{PWE}	WE Pulse Width	6		7		8		10		ns
t _{SD}	Data Set-up to Write End	4		5		6		7		ns
t _{HD}	Data Hold from Write End	0		0		0		0		ns
t _{LZWE}	WE HIGH to Low-Z ^[9]	3		3		3		3		ns
t _{HZWE}	WE LOW to High-Z ^[8, 9]		4		5		6		7	ns

Notes:

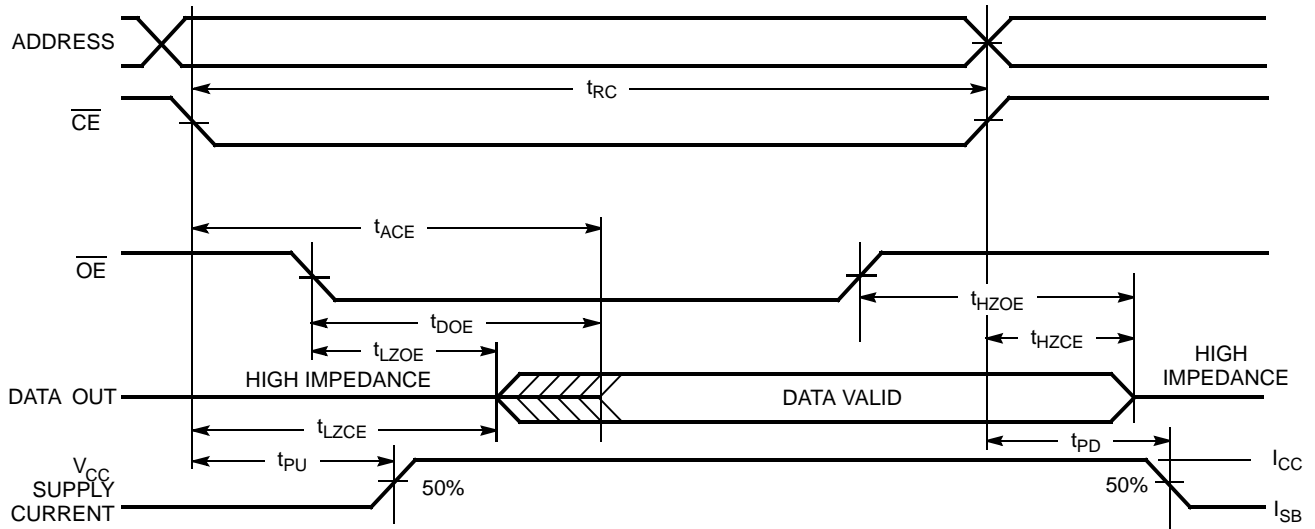
5. AC characteristics (except High-Z) for all 8-ns and 10-ns parts are tested using the load conditions shown in Figure (a). All other speeds are tested using the Thevenin load shown in Figure (b). High-Z characteristics are tested for all speeds using the test load shown in Figure (d).

Switching Waveforms

Read Cycle No. 1^[12, 13]

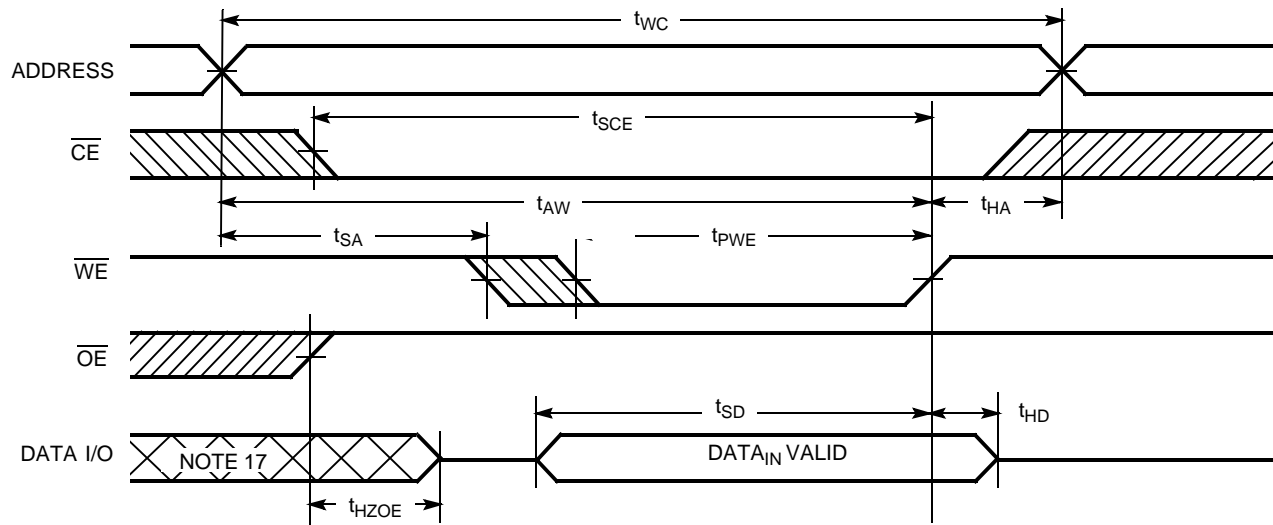
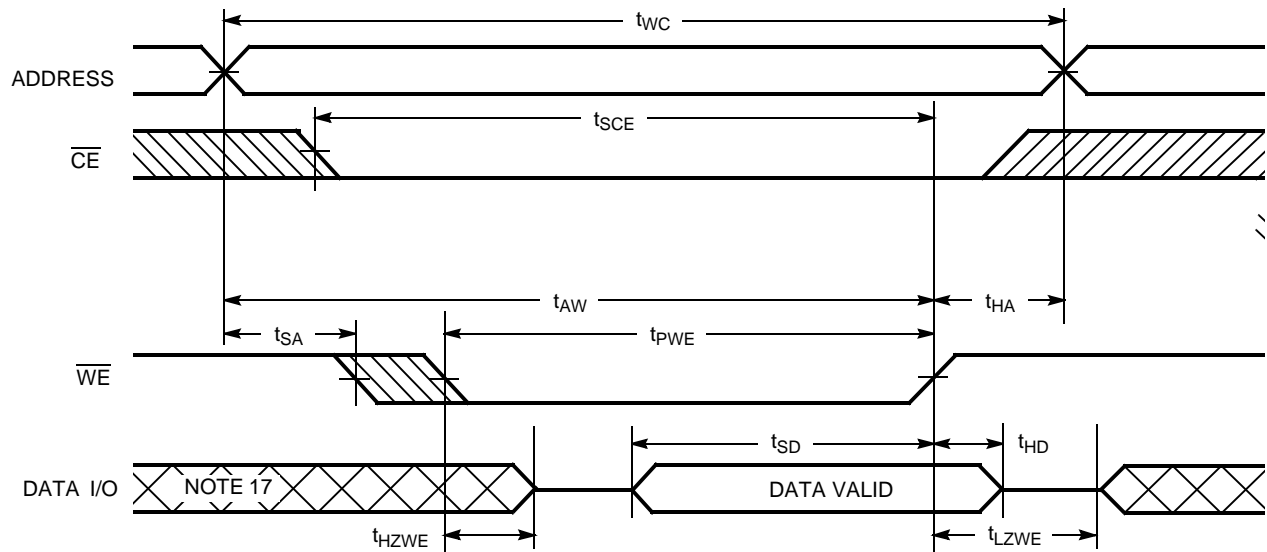


Read Cycle No. 2 (OE Controlled)^[13, 14]



Notes:

6. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V.
7. t_{POWER} gives the minimum amount of time that the power supply should be at stable, typical V_{CC} values until the first memory access can be performed.
8. t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
9. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
10. The internal Write time of the memory is defined by the overlap of \overline{CE} LOW, and \overline{WE} LOW. \overline{CE} and \overline{WE} must be LOW to initiate a Write, and the transition of either of these signals can terminate the Write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the Write.
11. The minimum Write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD} .
12. Device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
13. \overline{WE} is HIGH for Read cycle.

Switching Waveforms (continued)
Write Cycle No. 1 (\overline{WE} Controlled, \overline{OE} HIGH During Write)^[15, 16]

Write Cycle No. 2 (\overline{WE} Controlled, \overline{OE} LOW)^[16]

Notes:

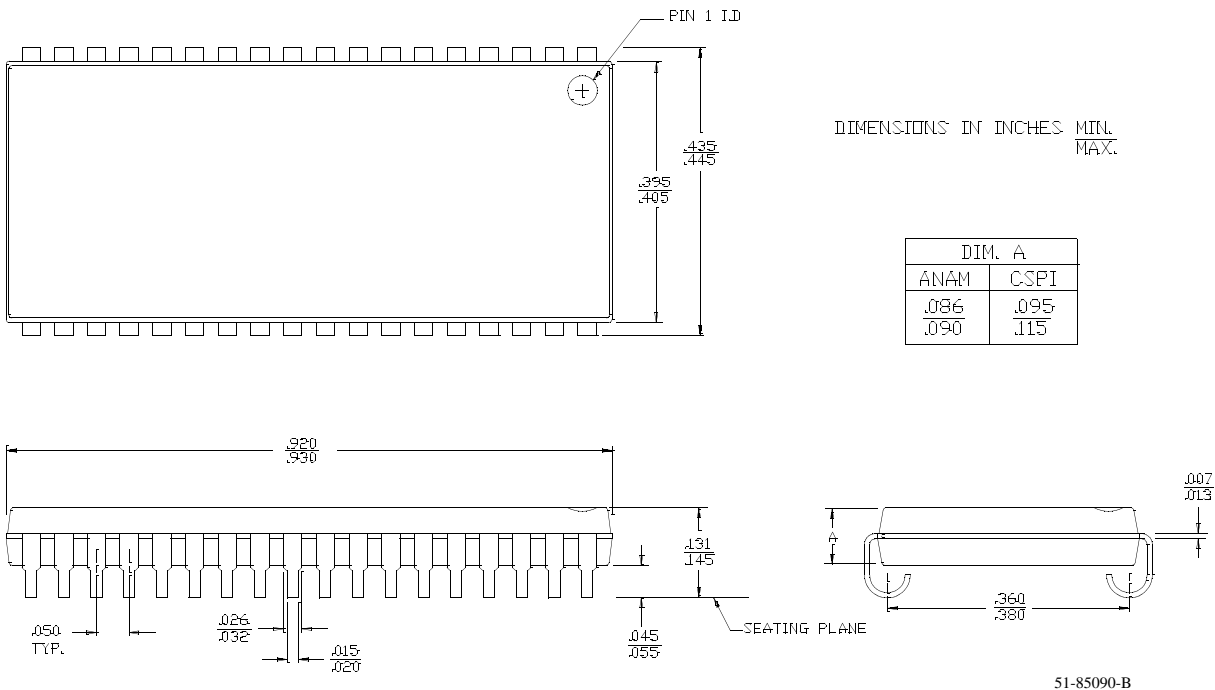
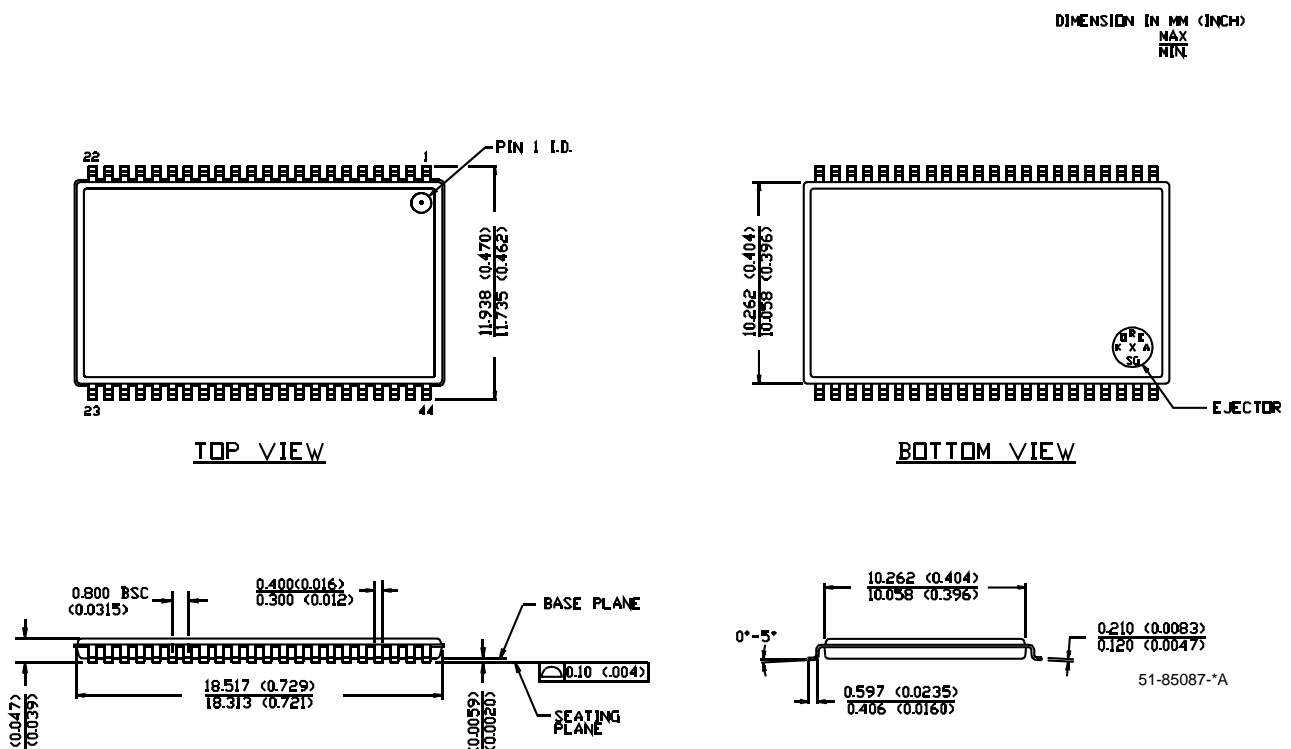
14. Address valid prior to or coincident with \overline{CE} transition LOW.
15. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
16. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high-impedance state.
17. During this period the I/Os are in the output state and input signals should not be applied.

Truth Table

CE	OE	WE	I/O ₀ –I/O ₇	Mode	Power
H	X	X	High-Z	Power-down	Standby (I _{SB})
L	L	H	Data Out	Read	Active (I _{CC})
L	X	L	Data In	Write	Active (I _{CC})
L	H	H	High-Z	Selected, Outputs Disabled	Active (I _{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C1049CV33-10VC	V36	36-lead (400-Mil) Molded SOJ	Commercial
	CY7C1049CV33-10ZC	Z44	44-pin TSOP II	
	CY7C1049CV33-10VI	V36	36-lead (400-Mil) Molded SOJ	Industrial
	CY7C1049CV33-10ZI	Z44	44-pin TSOP II	
12	CY7C1049CV33-12VC	V36	36-lead (400-Mil) Molded SOJ	Commercial
	CY7C1049CV33-12ZC	Z44	44-pin TSOP II	
	CY7C1049CV33-12VI	V36	36-lead (400-Mil) Molded SOJ	Industrial
	CY7C1049CV33-12ZI	Z44	44-pin TSOP II	
15	CY7C1049CV33-15VXC	V36	36-lead (400-Mil) Molded SOJ (Pb-Free)	Commercial
	CY7C1049CV33-15VC	V36	36-lead (400-Mil) Molded SOJ	
	CY7C1049CV33-15ZXC	Z44	44-pin TSOP II (Pb-Free)	
	CY7C1049CV33-15ZC	Z44	44-pin TSOP II	
	CY7C1049CV33-15VI	V36	36-lead (400-Mil) Molded SOJ	Industrial
	CY7C1049CV33-15ZI	Z44	44-pin TSOP II	
	CY7C1049CV33-15VE	V36	36-lead (400-Mil) Molded SOJ	Automotive
	CY7C1049CV33-15ZE	Z44	44-pin TSOP II	

Package Diagrams
36-Lead (400-Mil) Molded SOJ V36

44-pin TSOP II Z44


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Document History Page

Document Title: CY7C1049CV33 4-Mbit (512K x 8) Static RAM
Document Number: 38-05006

REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	112569	03/06/02	HGK	New Data Sheet
*A	114091	04/25/02	DFP	Changed Tpower unit from ns to μ s
*B	116479	09/16/02	CEA	Add applications foot note to data sheet, page 1.
*C	262949	See ECN	RKF	Added Automotive Specs to Datasheet Added Θ_{JA} and Θ_{JC} values on Page #3.